ITSS

24th International Travelling Summer School on Microwaves and Lightwaves 5-11 July 2014, Copenhagen, Denmark



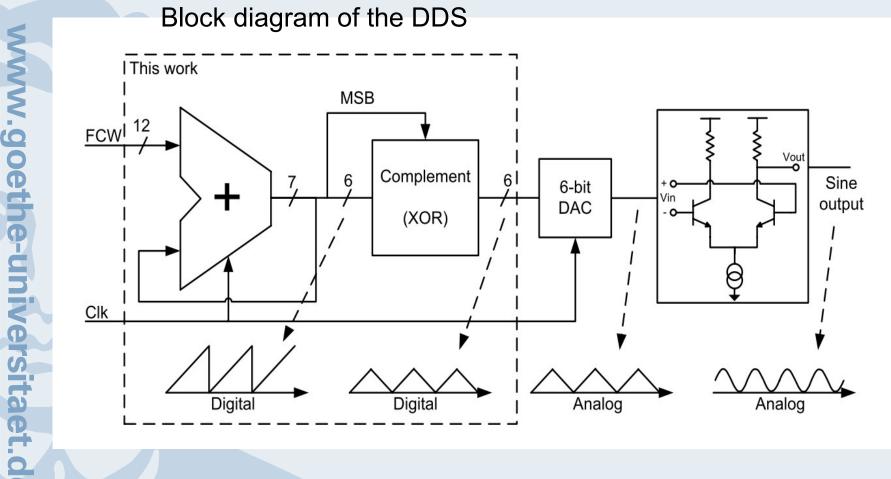


High Speed 12-bit Arbitrary Waveform Generator (AWG)

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Previous Work - Initial Point

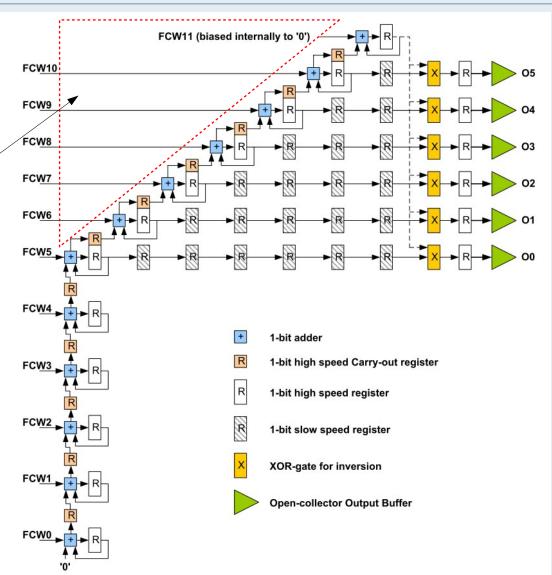






Main Part - The Accumulator

Omitted preskew registers lead to a phaseshift when switching the FCW



Goals



Enhancement of the accumulator

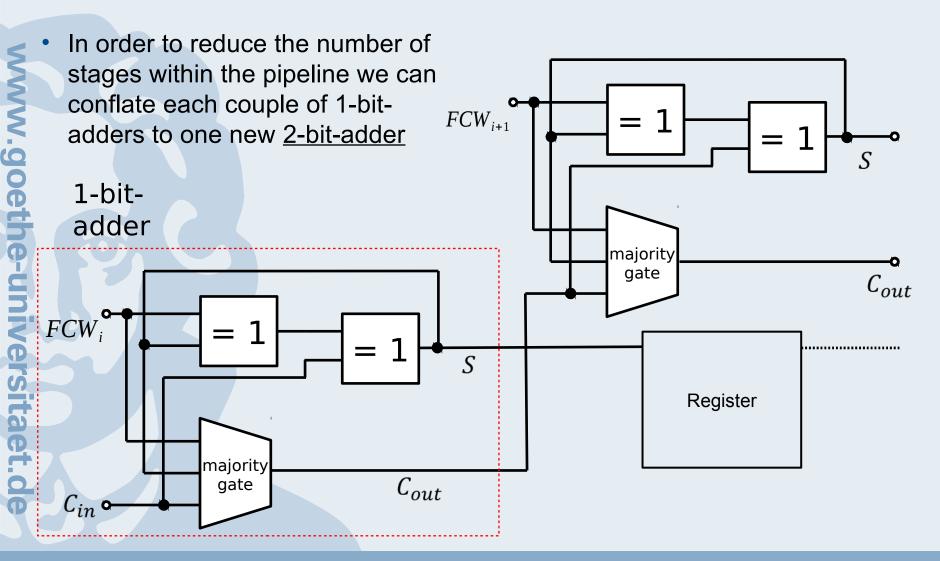
- Reduction of the power consumption (currently: ~1W)
- Providing a <u>Phase Control Word</u> (PCW) makes it possible to manipulate the phase of the output signal while the system is running
- Secondary: increasing the <u>clock frequency</u> (currently: 20GHz)

Bringing together the accumulator and the DAC on one chip

- IHP from Frankfurt (Oder) provides a 6-bit DAC that can be used as a "black box"
- In the previous work the accumulator was a separate chip

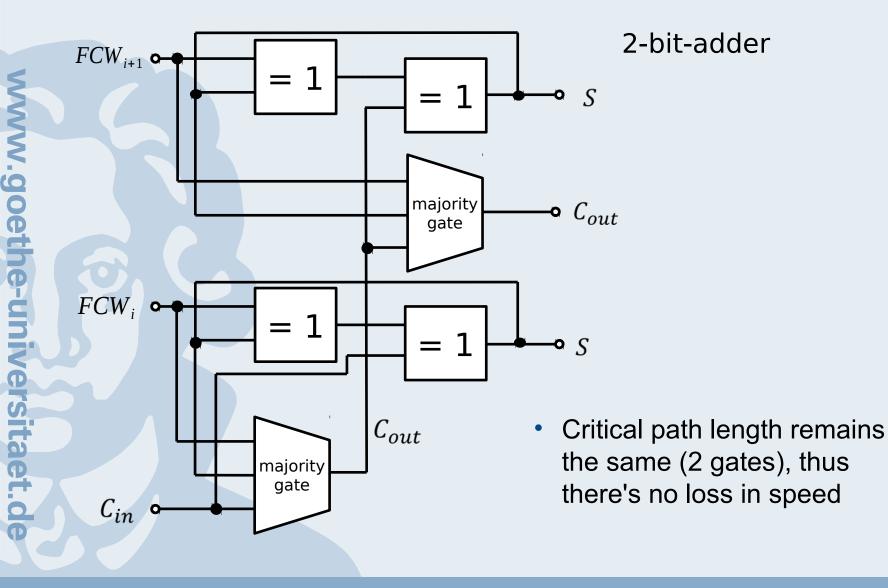




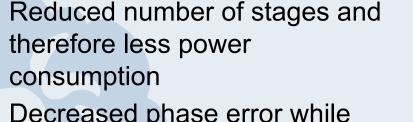


Current State - Accumulator





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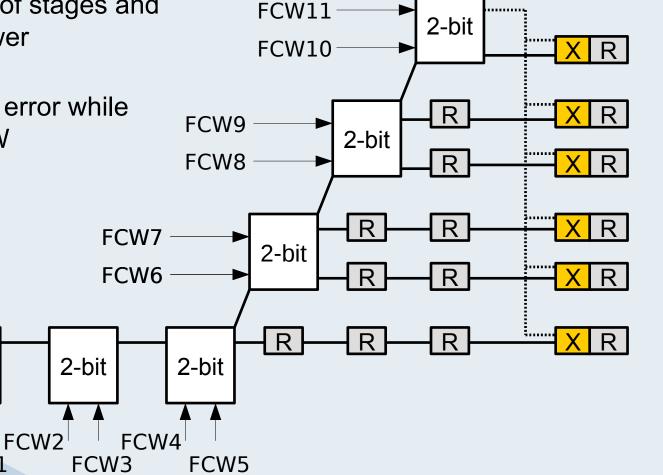


Decreased phase error while switching the FCW

2-bit

FCW1

FCW0

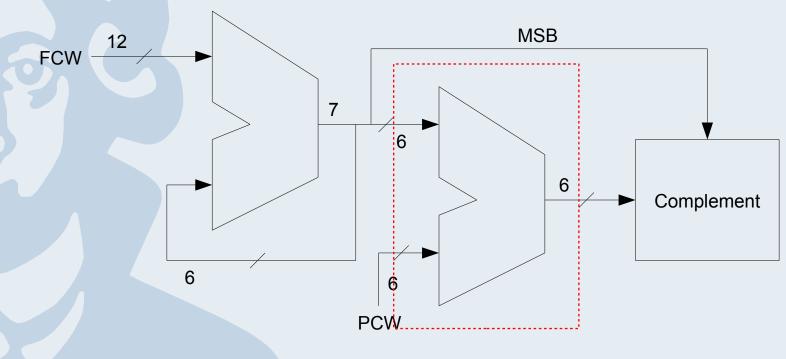






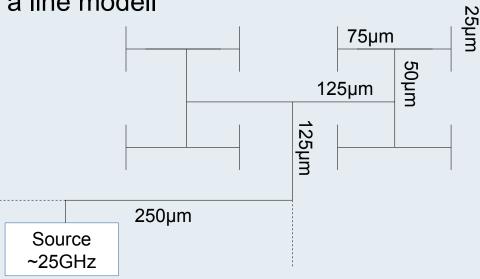
Current State - Accumulator

- In order to provide a PCW, it's necessary to include further adders within the DDS
- This way the DDS becomes an **A**rbitrary **W**aveform **G**enerator (AWG)





- Further important issue: clock distribution
- At high frequencies it's necessary to control the clock screw very carefully
- Therefore a <u>H-Tree</u> structure is used to ensure that the signal path length from the clock source to each gate is exactly the same
- Layout is finished, but not simulated yet
- For a realistic simulation a line modell will be used





- Clock source shell be integrated on the chip: therefore a <u>VCO (+PLL</u>) is needed to generate a stable clock signal @25-30GHz
- Using another technology to run the chip at higher frequencies
 - Currently: 0.25µm SiGe:C BiCMOS technology with npn-HBTs up to $f_T/f_{max} = 180/220 GHz$
 - Planned: 0.13µm technology with npn-HBTs up to
 - $f_T / f_{max} = 250 / 300 \, GHz$



